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Patrick P. Naulleau
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The CID Number appears on each page of the manuscript. The complete citation is used on the first page, and an abbreviated version on subsequent pages. Numbers in the index correspond to the last two digits of the six-digit CID Number.

Contents

Part One

xv *Conference Committee*

SESSION 1 INVITED I

- 8679 03 **Effects of multilayer period on EUVL imaging for 2X node and beyond (Invited Paper)** [8679-2]
S.-Y. Lee, H.-S. Seo, T.-G. Kim, S.-H. Kim, R. Chalykh, S.-S. Kim, C.-U. Jeon, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 8679 04 **Investigation of EUV pellicle feasibility (Invited Paper)** [8679-3]
L. Scaccabarozzi, D. Smith, P. R. Diago, E. Casimiri, N. Dziomkina, H. Meijer, ASML Netherlands B.V. (Netherlands)
- 8679 05 **EUV resist materials design for 15nm half pitch and below (Invited Paper)** [8679-4]
H. Tsubaki, S. Tarutani, N. Inoue, H. Takizawa, T. Goto, FUJIFILM Corp. (Japan)

SESSION 2 EUV RESISTS: JOINT SESSION WITH CONFERENCES 8679 AND 8682

- 8679 06 **Oxide nanoparticle EUV resists: toward understanding the mechanism of positive and negative tone patterning** [8679-5]
S. Chakrabarty, C. Ouyang, M. Krysak, M. Trikeriotis, Cornell Univ. (United States); K. Cho, SEMATECH Inc. (United States); E. P. Giannelis, C. K. Ober, Cornell Univ. (United States)
- 8679 07 **Effect of leaving group design on EUV lithography performance** [8679-6]
O. Ongayi, V. Jain, S. Coley, D. Valeri, A. Kwok, D. Quach, M. Wagner, J. Cameron, J. Thackeray, Dow Electronic Materials (United States)

SESSION 3 SOURCES

- 8679 0A **LPP-EUV light source development for high volume manufacturing lithography** [8679-9]
H. Mizoguchi, H. Nakarai, T. Abe, T. Ohta, K. M. Nowak, Y. Kawasuji, H. Tanaka, Y. Watanabe, T. Hori, T. Kodama, Y. Shiraishi, T. Yanagida, T. Yamada, T. Yamazaki, S. Okazaki, T. Saitou, Gigaphoton Inc. (Japan)
- 8679 0B **Advances in computer simulations of LPP sources for EUV lithography** [8679-10]
A. Hassanein, T. Szyuk, Purdue Univ. (United States)

- 8679 0C **Lifetime and refurbishment of multilayer LPP collector mirrors** [8679-12]
T. Feigl, M. Perske, H. Pauer, T. Fiedler, S. Yulin, N. Kaiser, A. Tünnermann, Fraunhofer-Institut für Angewandte Optik und Feinmechanik (Germany); N. R. Böwering, A. I. Ershov, S. de Dea, K. Hoffmann, B. La Fontaine, I. V. Fomenkov, D. C. Brandt, Cymer, Inc. (United States)
- 8679 0D **Contamination concerns at the intermediate focus of an extreme ultraviolet light source** [8679-13]
D. N. Ruzic, J. Sporre, D. Elg, D. Curreli, Univ. of Illinois at Urbana-Champaign (United States)

SESSION 4 MASK I

- 8679 0F **Dressed-photon nanopolishing for extreme ultraviolet mask substrate defect mitigation** [8679-14]
R. Teki, A. J. Kadaksham, F. Goodwin, SEMATECH Inc. (United States); T. Yatsui, The Univ. of Tokyo (Japan) and Japan Science and Technology Agency (Japan); M. Ohtsu, The Univ. of Tokyo (Japan)
- 8679 0G **EUV mask defect analysis from mask to wafer printing** [8679-15]
Y. Hyun, K. Seo, K. Kim, I. Lee, B. Lee, S. Koo, J. Lee, S. Kim, S. Kim, M. Kim, H. Kang, Hynix Semiconductor Inc. (Korea, Republic of)
- 8679 0H **Defect printability comparing actinic printing with advanced simulation for EUV masks** [8679-16]
I.-Y. Jang, R. Teki, V. Jindal, F. Goodwin, SEMATECH Inc. (United States); M. Satake, Y. Li, D. Peng, Luminescent Technologies (United States); S. Huh, S.-S. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 8679 0I **EUV actinic blank inspection: from prototype to production** [8679-17]
A. Tchikoulaeva, Lasertec U.S.A., Inc. Zweigniederlassung Deutschland (Germany); H. Miyai, T. Suzuki, K. Takehisa, H. Kusunose, Lasertec Corp. (Japan); T. Yamane, T. Terasawa, H. Watanabe, S. Inoue, I. Mori, EUVL Infrastructure Development Ctr., Inc. (Japan)

SESSION 5 RESIST OUTGASSING

- 8679 0K **Relationship between resist related outgassing and witness sample contamination in the NXE outgas qualification using electrons and EUV** [8679-19]
I. Pollentier, R. Lokasani, R. Gronheid, IMEC (Belgium); S. Hill, C. Tarrío, T. Lucatorto, National Institute of Standards and Technology (United States)
- 8679 0L **Resist outgassing contamination growth results using both photon and electron exposures** [8679-20]
G. Denbeaux, Y. Kandel, G. Kane, D. Alvarado, M. Upadhyaya, Y. Khopkar, Univ. at Albany (United States); A. Friz, K. Petrillo, J. Sohn, C. Sarma, D. Ashworth, SEMATECH Inc. (United States)

- 8679 OM **Study of EUV outgassing spatial distribution toward witness plate in the EUV outgas tester** [8679-21]
Y. Kikuchi, E. Shiobara, H. Tanaka, I. Takagi, K. Katayama, N. Sugie, T. Takahashi, S. Inoue, EUVL Infrastructure Development Ctr., Inc. (Japan); T. Watanabe, T. Harada, H. Kinoshita, Univ. of Hyogo (Japan)
- 8679 OO **Balancing lithographic performance and resist outgassing in EUV resists** [8679-23]
S.-H. Chang, S.-F. Chen, Y.-Y. Chen, M.-C. Chien, S.-C. Chien, T.-L. Lee, J. J.-H. Chen, A. Yen, TSMC Inc. (Taiwan)

SESSION 6 OPTICS AND METROLOGY

- 8679 OP **EUVL resist-based aberration metrology** [8679-24]
G. L. Fenger, Rochester Institute of Technology (United States); S. Raghunathan, L. Sun, O. R. Wood, GLOBALFOUNDRIES Inc. (United States); B. W. Smith, Rochester Institute of Technology (United States)
- 8679 OQ **In-situ optical testing of exposure tools via localized wavefront curvature sensing** [8679-25]
R. Miyakawa, Lawrence Berkeley National Lab. (United States); X. Zhou, SEMATECH Inc. (United States); M. Goldstein, SEMATECH Inc. (United States) and Intel Corp. (United States); D. Ashworth, K. Cummings, Y.-J. Fan, SEMATECH Inc. (United States); Y. Shroff, Intel Corp. (United States); G. Denbeaux, Y. Kandel, Univ. at Albany (United States); P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 8679 OT **Application of phase shift focus monitor in EUVL process control** [8679-28]
L. Sun, S. Raghunathan, GLOBALFOUNDRIES Inc. (United States); V. Jindal, SEMATECH Inc. (United States); E. Gullikson, Lawrence Berkeley National Lab. (United States); P. Mangat, GLOBALFOUNDRIES Inc. (United States); I. Mochi, K. A. Goldberg, M. P. Benk, Lawrence Berkeley National Lab. (United States); O. Kritsun, T. Wallow, D. Civay, O. Wood, GLOBALFOUNDRIES Inc. (United States)

SESSION 7 OPC AND MODELING

- 8679 OU **EUV multilayer defect compensation (MDC) by absorber pattern modification, film deposition, and multilayer peeling techniques** [8679-29]
L. Pang, M. Satake, Y. Li, P. Hu, D. Peng, D. Chen, V. Tolani, Luminescent Technologies (United States)
- 8679 OV **Evaluation of methods to improve EUV OPC model accuracy** [8679-30]
T. H. Coskun, C. Clifford, G. Fenger, GLOBALFOUNDRIES Inc. (United States); G. S. Chua, GLOBALFOUNDRIES Singapore (Singapore); K. Standiford, R. Schlieff, C. Higgins, Y. Zou, GLOBALFOUNDRIES Inc. (United States)
- 8679 OW **Fast 3D thick mask model for full-chip EUVL simulations** [8679-31]
P. Liu, X. Xie, W. Liu, K. Gronlund, ASML Brion Technologies (United States)

- 8679 0X **Process and proximity correction, and verification for extreme ultraviolet lithography** [8679-32]
G. Perçin, Cadence Design Systems, Inc. (United States); H. Dai, Applied Materials, Inc. (United States); H.-T. Huang, A. Liu, A. Mokhberi, X. Zheng, Cadence Design Systems, Inc. (United States); C. Ngai, Applied Materials, Inc. (United States)
- 8679 0Y **Modeling strategies for EUV mask multilayer defect dispositioning and repair** [8679-33]
A. Erdmann, P. Evanschitzky, Fraunhofer Institute for Integrated Systems and Device Technology (Germany); T. Bret, Carl Zeiss SMS GmbH (Germany); R. Jonckheere, IMEC (Belgium)

SESSION 8 EUV RESISTS

- 8679 10 **Evaluation of EUV resist performance with interference lithography towards 11 nm half-pitch and beyond** [8679-35]
Y. Ekinici, M. Vockenhuber, M. Hojeij, L. Wang, N. Mojarad, Paul Scherrer Institute (Switzerland)
- 8679 11 **Resist process applications to improve EUV patterning** [8679-36]
K. Petrillo, K. Cho, A. Friz, C. Montgomery, D. Ashworth, M. Neisser, S. Wurm, SEMATECH Inc. (United States); T. Saito, L. Huli, A. Ko, A. Metz, TEL Technology Ctr., America, LLC (United States)
- 8679 12 **Development of molecular resist derivatives for EUV lithography** [8679-37]
D. P. Green, The Dow Chemical Co. (United States); V. Jain, Dow Electronic Materials (United States); B. Bailey, The Dow Chemical Co. (United States); M. Wagner, Dow Electronic Materials (United States); M. Clark, Dow Advanced Materials (United States); D. Valeri, Dow Electronic Materials (United States); S. Lakso, The Dow Chemical Co. (United States)
- 8679 13 **Relationship between stochastic effect and resist pattern defect in extreme ultraviolet lithography** [8679-38]
T. Kozawa, Osaka Univ. (Japan); J. J. Santillan, T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 14 **EUV sensitive Si containing hard mask (Si-HM) for PTD and NTD process in EUVL** [8679-39]
W. Shibayama, S. Shigaki, R. Sakamoto, R. Onishi, H. Yaguchi, Nissan Chemical Industries, Ltd. (Japan); B. C. Ho, Nissan Chemical Taiwan (Taiwan)

SESSION 9 HIGH NA AND MAGNIFICATION

- 8679 15 **Mask effects for high-NA EUV: impact of NA, chief-ray-angle, and reduction ratio (Invited Paper)** [8679-40]
J. T. Neumann, P. Gräupner, W. Kaiser, R. Garreis, Carl Zeiss SMT GmbH (Germany); B. Geh, Carl Zeiss SMT (United States)

- 8679 16 **Considerations for high-numerical aperture EUV lithography (Invited Paper)** [8679-41]
H. J. Levinson, P. Mangat, T. Wallow, L. Sun, P. Ackmann, S. Meyers, GLOBALFOUNDRIES Inc. (United States)
- 8679 17 **Projection optics for extreme ultraviolet lithography (EUVL) micro-field exposure tools (METs) with a numerical aperture of 0.5** [8679-42]
H. Glatzel, Zygo Corp. (United States); D. Ashworth, SEMATECH Inc. (United States); M. Bremer, R. Chin, Zygo Corp. (United States); K. Cummings, SEMATECH Inc. (United States); L. Girard, Zygo Corp. (United States); M. Goldstein, SEMATECH Inc. (United States); E. Gullikson, Lawrence Berkeley National Lab. (United States); R. Hudyma, Hyperion Development LLC (United States); J. Kennon, B. Kestner, L. Marchetti, Zygo Corp. (United States); P. Naulleau, Lawrence Berkeley National Lab. (United States); R. Soufli, Lawrence Livermore National Lab. (United States); E. Spiller, Spiller X-Ray Optics (United States)
- 8679 18 **Mask 3D effects and compensation for high NA EUV lithography** [8679-43]
S. Raghunathan, GLOBALFOUNDRIES Inc. (United States); G. McIntyre, IBM Corp. (United States); G. Fenger, O. Wood, GLOBALFOUNDRIES Inc. (United States)

SESSION 10 MASK II

- 8679 19 **Commissioning an EUV mask microscope for lithography generations reaching 8 nm** [8679-44]
K. A. Goldberg, I. Mochi, M. Benk, A. P. Allezy, M. R. Dickinson, C. W. Cork, D. Zehm, J. B. Macdougall, E. Anderson, F. Salmassi, W. L. Chao, V. K. Vytla, E. M. Gullikson, J. C. DePonte, M. S. G. Jones, D. Van Camp, J. F. Gamsby, W. B. Ghiorso, H. Huang, W. Cork, E. Martin, Lawrence Berkeley National Lab. (United States); E. Van Every, E. Acome, Advanced Design Consulting USA, Inc. (United States); V. Milanovic, Mirrorcle Technologies, Inc. (United States); R. Delano, P. P. Naulleau, S. B. Rekawa, Lawrence Berkeley National Lab. (United States)
- 8679 1B **Experimental phase defect printability evaluation using a programmed phase defect in EUVL mask** [8679-46]
T. Terasawa, T. Amano, S. Oh, T. Yamane, H. Watanabe, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 1D **Challenges in EUV mask blank deposition for high volume manufacturing** [8679-48]
V. Jindal, P. Kearney, A. Antohe, M. Godwin, A. John, R. Teki, J. Harris-Jones, E. Stinzianni, F. Goodwin, SEMATECH Inc. (United States)
- 8679 1E **Extending Ru capping layer durability under physical force cleaning** [8679-49]
S. Singh, U. Dietze, SUSS MicroTec Inc. (United States); P. Dress, SUSS MicroTec Photomask Equipment GmbH & Co. KG (Germany)

Part Two

SESSION 11 INVITED II

- 8679 1F **ASML's NXE platform performance and volume introduction (Invited Paper)** [8679-50]
R. Peeters, S. Lok, E. van Alphen, N. Harned, ASML Netherlands B.V. (Netherlands); P. Kuerz, M. Lowisch, Carl Zeiss SMT AG (Germany); H. Meijer, D. Ockwell, E. van Setten, G. Schiffelers, J.-W. van der Horst, J. Stoeldraijer, R. Kazinczi, R. Droste, H. Meiling, R. Kool, ASML Netherlands B.V. (Netherlands)
- 8679 1G **CO₂/Sn LPP EUV sources for device development and HVM (Invited Paper)** [8679-51]
D. C. Brandt, I. V. Fomenkov, N. R. Farrar, B. La Fontaine, D. W. Myers, D. J. Brown, A. I. Ershov, R. L. Sandstrom, G. O. Vaschenko, N. R. Böwering, P. Das, V. B. Fleurov, K. Zhang, S. N. Srivastava, I. Ahmad, C. Rajyaguru, S. De Dea, W. J. Dunstan, P. Baumgart, T. Ishihara, R. D. Simmons, R. N. Jacques, R. A. Bergstedt, P. I. Porshnev, C. J. Wittak, R. J. Rafac, J. Grava, A. A. Schafgans, Y. Tao, K. Hoffmann, T. Ishikawa, D. R. Evans, S. D. Rich, Cymer, Inc. (United States)
- 8679 1H **Optics for ASML's NXE:3300B platform (Invited Paper)** [8679-52]
M. Lowisch, P. Kuerz, O. Conradi, G. Wittich, W. Seitz, W. Kaiser, Carl Zeiss SMT GmbH (Germany)
- 8679 1I **Through-focus EUV multilayer defect repair with nanomachining (Invited Paper)** [8679-53]
G. McIntyre, E. Gallagher, IBM Microelectronics (United States); T. Robinson, RAVE LLC (United States); A. C. Smith, M. Lawliss, IBM Microelectronics (United States); J. LeClaire, R. Bozak, R. White, M. Archuletta, RAVE LLC (United States)
- 8679 1J **Patterning challenges of EUV lithography for 1X-nm node DRAM and beyond (Invited Paper)** [8679-54]
T.-S. Eom, H.-I. Kim, C.-K. Kang, Y.-J. Ryu, S.-H. Hwang, H.-H. Lee, H.-Y. Lim, J.-S. Park, N.-J. Kwak, S. Park, Hynix Semiconductor Inc. (Korea, Republic of)
- 8679 1K **Towards manufacturing a 10nm node device with complementary EUV lithography (Invited Paper)** [8679-55]
J. V. Hermans, IMEC (Belgium); H. Dai, Applied Materials, Inc. (United States); A. Niroomand, Micron Technology, Inc. (United States); D. Laidler, M. Mao, IMEC (Belgium); Y. Chen, Applied Materials, Inc. (United States); P. Leray, IMEC (Belgium); C. Ngai, Applied Materials, Inc. (United States); S. Cheng, IMEC (Belgium)

POSTER SESSION

- 8679 1L **Limitation of OAI + AHPSPM in EUVL** [8679-56]
S.-S. Yu, Y.-C. Lu, C.-T. Shih, J. J. H. Chen, A. Yen, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)

- 8679 1M **Experimental verification of EUV mask limitations at high numerical apertures** [8679-57]
R. Chao, Lawrence Berkeley National Lab. (United States) and Univ. of California, Berkeley (United States); P. Graeupner, Carl Zeiss SMT GmbH (Germany); E. Gullikson, Lawrence Berkeley National Lab. (United States); S.-S. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); J.-T. Neumann, Carl Zeiss SMT GmbH (Germany); R. Miyakawa, Lawrence Berkeley National Lab. (United States); H.-S. Seo, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); A. Neureuther, Univ. of California, Berkeley (United States); P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 8679 1N **Homogeneity improvement of TiO₂-SiO₂ glass synthesized by the soot method and its evaluation using the ultrasonic measurement system** [8679-58]
M. Kawagishi, J. Konishi, M. Takata, Asahi Glass Co., Ltd. (Japan); M. Arakawa, Y. Ohashi, J. Kushibiki, Tohoku Univ. (Japan)
- 8679 1O **Inspection and compositional analysis of sub-20 nm EUV mask blank defects by thin film decoration technique** [8679-59]
V. Jindal, A. John, J. Harris-Jones, P. Kearney, A. Antohe, E. Stinzianni, F. Goodwin, SEMATECH Inc. (United States); T. Onoue, HOYA Corp. (Japan)
- 8679 1P **Propagation of surface topography of EUV blank substrate through multilayer and impact of phase defect structure on wafer image** [8679-60]
T. Amano, T. Terasawa, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 1Q **Modeling studies on alternative EUV mask concepts for higher NA** [8679-61]
A. Erdmann, T. Fühner, P. Evanschitzky, Fraunhofer Institute for Integrated Systems and Device Technology (Germany); J. T. Neumann, J. Ruoff, P. Gräupner, Carl Zeiss SMT GmbH (Germany)
- 8679 1R **Low thermal expansion material (LTEM) cleaning and optimization for extreme ultraviolet (EUV) blank deposition** [8679-62]
A. J. Kadaksham, R. Teki, M. Godwin, M. House, F. Goodwin, SEMATECH Inc. (United States)
- 8679 1T **Evaluation of novel projection electron microscopy (PEM) optics for EUV mask inspection** [8679-64]
R. Hirano, S. Iida, T. Amano, T. Terasawa, H. Watanabe, EUVL Infrastructure Development Ctr., Inc. (Japan); K. Terao, EBARA Corp. (Japan)
- 8679 1U **Registration accuracy improvement of fiducial mark on EUVL mask with MIRAI EUV ABI prototype** [8679-65]
T. Murachi, T. Amano, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 1V **Study on EUV mask defect inspection with hp 16nm node using simulated projection electron microscope images** [8679-66]
S. Iida, T. Amano, R. Hirano, T. Terasawa, H. Watanabe, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 1W **Development of 3D Monte Carlo simulations for predicting multilayer geometry of pit-type EUV defects** [8679-67]
R. F. Spivey, Rensselaer Polytechnic Institute (United States); R. Teki, SEMATECH Inc. (United States); T.-M. Lu, Rensselaer Polytechnic Institute (United States)

- 8679 1X **Effect of phase defect shape on ABI signal intensity and defect image intensity on wafer with simulation** [8679-68]
N. Takagi, T. Terasawa, Y. Arisawa, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 1Y **Mathematical model for calculating speckle contrast through focus** [8679-69]
R. A. Claus, A. R. Neureuther, Univ. of California, Berkeley (United States); P. P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 8679 1Z **Evaluating the effect of EUV multilayer buried defects on feature printability using a stochastic resist model** [8679-70]
T. Graves, J. Biafore, M. Smith, S. Robertson, C. Fang, KLA-Tencor Corp. (United States)
- 8679 20 **Effects of varying the parameters in witness-sample-based photoresist outgas testing: dependence of the carbon growth on pumping speed and the dose, time, and area of resist exposure** [8679-71]
C. Tarrio, R. F. Berg, S. B. Hill, S. Grantham, N. S. Faradzhev, T. B. Lucatorto, National Institute of Standards and Technology (United States)
- 8679 21 **Status of EUV reflectometry at PTB** [8679-72]
C. Laubis, A. Barboutis, M. Biel, C. Buchholz, B. Dubrau, A. Fischer, A. Hesse, J. Puls, C. Stadelhoff, V. Soltwisch, F. Scholze, Physikalisch-Technische Bundesanstalt (Germany)
- 8679 22 **Hartmann wavefront sensor for EUV radiation** [8679-73]
K. Mann, B. Flöter, T. Mey, B. Schäfer, Laser-Lab. Göttingen e.V. (Germany); B. Keitel, E. Plönjes, K. Tiedtke, Deutsches Elektronen-Synchrotron (Germany)
- 8679 23 **A reverse design method for EUV lithography illumination system** [8679-74]
Q. Mei, Y. Li, F. Liu, Beijing Institute of Technology (China)
- 8679 24 **Patterning at 6.5 nm wavelength using interference lithography** [8679-75]
N. Mojarad, M. Vockenhuber, L. Wang, B. Terhalle, Y. Ekinici, Paul Scherrer Institute (Switzerland)
- 8679 25 **Simulation analysis of LER and dose tradeoffs for EUV resists with photo-decomposable quenchers** [8679-76]
S. Bhattarai, A. R. Neureuther, Univ. of California, Berkeley (United States) and Lawrence Berkeley National Lab. (United States); P. P. Naulleau, Lawrence Berkeley National Lab. (United States)
- 8679 26 **Relation between sensitivity and resolution in polymer bound PAGs and polymer blend PAGs** [8679-77]
S. Enomoto, T. N. Dang, C. Q. Dinh, S. Tagawa, Osaka Univ. (Japan) and Japan Science and Technology Agency (Japan)
- 8679 28 **Stochastic resist patterning simulation using attenuated PSM for EUV lithography** [8679-79]
S. Hong, S. Jeong, J. U. Lee, S. M. Lee, J. Kim, Hanyang Univ. (Korea, Republic of); J. Doh, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); J. Ahn, Hanyang Univ. (Korea, Republic of)

- 8679 29 **Quencher distribution engineering for out-of-band insensitive EUV resists: experiments and stochastic simulation** [8679-80]
S.-C. Chien, S.-H. Chang, J.-C. Wu, J. J.-H. Chen, A. Yen, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)
- 8679 2A **Prediction of resist sensitivity for 13.5-nm EUV and 6.x-nm EUV extension from sensitivity for EBL** [8679-81]
T. G. Oyama, Japan Atomic Energy Agency (Japan); A. Oshima, T. N. Dang, Osaka Univ. (Japan) and JST-CREST (Japan); S. Enomoto, Osaka Univ. (Japan); M. Washio, Waseda Univ. (Japan); S. Tagawa, Osaka Univ. (Japan) and JST-CREST (Japan)
- 8679 2B **Study of LWR reduction and pattern collapse suppression for 16nm node EUV resists** [8679-82]
E. Shiobara, Y. Kikuchi, T. Itani, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 2C **Reaction mechanisms of various chemically amplified EUV and EB resist** [8679-83]
S. Enomoto, A. Oshima, S. Tagawa, Osaka Univ. (Japan) and JST-CREST (Japan)
- 8679 2D **Development of an atomic hydrogen system for treatment of EUV mask blanks** [8679-84]
T. R. Mowll, Univ. at Albany (United States); A. J. Kadaksham, SEMATECH Inc. (United States); Z. R. Robinson, Univ. at Albany (United States) and SEMATECH Inc. (United States); S. Mead, C. A. Ventrice Jr., Univ. at Albany (United States); F. Goodwin, SEMATECH Inc. (United States)
- 8679 2E **Resist outgassing characterization based on the resist compositions and process** [8679-85]
N. Sugie, T. Takahashi, K. Katayama, I. Takagi, Y. Kikuchi, H. Tanaka, E. Shiobara, S. Inoue, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 2H **Collector optic in-situ Sn removal using hydrogen plasma** [8679-88]
J. R. Sporre, D. Elg, D. N. Ruzic, Univ. of Illinois at Urbana-Champaign (United States); S. N. Srivastava, I. V. Fomenkov, D. C. Brandt, Cymer, Inc. (United States)
- 8679 2I **Laser produced plasma EUV light source for EUVL patterning at 20nm node and beyond** [8679-89]
I. V. Fomenkov, D. C. Brandt, N. R. Farrar, B. La Fontaine, N. R. Böwering, D. J. Brown, A. I. Ershov, D. W. Myers, Cymer, Inc. (United States)
- 8679 2K **Important processes in modeling and optimization of EUV lithography sources** [8679-91]
T. Sizyuk, A. Hassanein, Purdue Univ. (United States)
- 8679 2M **Magnetic mitigation of debris for EUV sources** [8679-93]
D. Elg, J. Sporre, D. Curreli, D. N. Ruzic, Univ. of Illinois at Urbana-Champaign (United States); K. R. Umstadter, KLA-Tencor Corp. (United States)

- 8679 2N **Enhancing resolution with pupil filtering for projection printing systems with fixed or restricted illumination angular distribution** [8679-94]
G. McIntyre, IBM Corp. (United States); L. Teeuwen, ASML US, Inc. (United States); E. Sohmen, Carl Zeiss SMT GmbH (Germany); O. Wood, GLOBALFOUNDRIES Inc. (United States); D. Corliss, IBM Corp. (United States); T. van den Akker, S. Bouten, E. van Setten, O. Voznyi, S.-I. Han, ASML US, Inc. (United States); H. Bieg, Carl Zeiss SMT GmbH (Germany); M. Burkhardt, K. Petrillo, Z. J. Qi, A. Friz, IBM Corp. (United States)
- 8679 2O **Roughness and variability in EUV lithography: Who is to blame? (part 1)** [8679-95]
A. Vaglio Pret, R. Gronheid, IMEC (Belgium); T. R. Younkin, IMEC (Belgium) and Intel Corp. (United States); G. Winroth, IMEC (Belgium); J. J. Biafore, KLA-Tencor Corp. (United States); Y. Anno, K. Hoshiko, IMEC (Belgium) and JSR Micro N.V. (Belgium); V. Constantoudis, National Ctr. for Scientific Research Demokritos (Greece)
- 8679 2Q **7nm node EUV predictive study of mask LER transference to wafer** [8679-97]
D. Civay, GLOBALFOUNDRIES Inc. (United States); E. Nash, U. Klostermann, Synopsys GmbH (Germany); T. Wallow, P. Mangat, H. P. Koh, GLOBALFOUNDRIES Inc. (United States); P. Brooker, Synopsys (United States); J. Siebert, Synopsys GmbH (Germany); H. J. Levinson, GLOBALFOUNDRIES Inc. (United States)
- 8679 2R **Silica aerogel can capture flying particles in EUV tools** [8679-98]
K. Ota, J. Inoue, Nikon Corp. (Japan)
- 8679 2S **Impact of EUV mask roughness on lithography performance** [8679-99]
Y. Arisawa, T. Terasawa, H. Watanabe, EUVL Infrastructure Development Ctr., Inc. (Japan)
- 8679 2T **Track processing optimizations for different EUV resist platforms: preparing for a NXE:3300 baseline process** [8679-100]
P. Foubert, IMEC (Belgium); K. Matsunaga, IMEC (Belgium) and Tokyo Electron Kyushu Ltd. (Japan); H. Shite, T. Shimoaoki, Tokyo Electron Kyushu Ltd. (Japan); K. Nafus, IMEC (Belgium) and Tokyo Electron Kyushu Ltd. (Japan); A.-M. Goethals, D. Van Den Heuvel, J. Hermans, E. Hendrickx, IMEC (Belgium); H. Kosugi, Tokyo Electron Kyushu Ltd. (Japan)
- 8679 2U **Simulation-assisted layout biasing in EUV lithography and prediction of an optimum resist parameter space** [8679-101]
C. Sarma, SEMATECH Inc. (United States); J. Biafore, KLA-Tencor Corp. (United States); K. Cho, K. Petrillo, M. Neisser, SEMATECH Inc. (United States)
- 8679 2V **Deep ultraviolet out-of-band characterization of EUVL scanners and resists** [8679-102]
G. F. Lorusso, IMEC (Belgium); T. Matsumiya, J. Iwashita, T. Hirayama, Tokyo Ohka Kogyo Co., Ltd. (Japan); E. Hendrickx, IMEC (Belgium)
- 8679 2W **Investigation of coat-develop track system for EUV resist processing** [8679-104]
M. Harumoto, O. Tamada, T. Miyagi, K. Kaneyama, A. Morita, C. Pieczulewski, M. Asai, SOKUDO Co. Ltd. (Japan)
- 8679 2X **Heat behavior of extreme-ultraviolet pellicle including mesh support** [8679-105]
I.-S. Kim, E.-J. Kim, J.-W. Kim, H.-K. Oh, Hanyang Univ. (Korea, Republic of)

- 8679 2Y **The need for EUV lithography at advanced technology for sustainable wafer cost** [8679-107]
A. Mallik, W. Vansumere, J. Ryckaert, A. Mercha, N. Horiguchi, S. Demuynck, J. Bömmels, T. Zsolt, G. Vandenberghe, K. Ronse, A. Thean, D. Verkest, H. Lebon, A. Steegen, IMEC (Belgium)
- 8679 2Z **The study of novel PAG containing acid amplifier in EUV resist material** [8679-108]
H. S. Joo, J. H. Kim, J. H. Han, C. W. Bae, J. B. Shin, H. S. Lim, S. D. Cho, S. M. Kim, Korea Kumho Petrochemical Co., Ltd. (Korea, Republic of)
- 8679 34 **Optimizing XPS tool performance for characterizing trace contamination elements for EUV resist outgas testing** [8679-113]
M. Upadhyaya, Y. Kandel, G. Denbeaux, Univ. at Albany (United States); C. Montgomery, Y.-J. Fan, SEMATECH Inc. (United States)
- 8679 37 **Effect of cleaning on EUV masks** [8679-116]
J. W. Roberts, n&k Technology, Inc. (United States)

Author Index

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 Republic of)
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Session Chairs

- 1 Invited I
Jos P. Benschop, ASML Netherlands B.V. (Netherlands)
Shinji Okazaki, Gigaphoton Inc. (Japan)
- 2 EUV Resists: Joint Session with Conferences 8679 and 8682
Robert L. Brainard, University at Albany (United States)
George G. Barclay, Dow Advanced Materials (United States)
- 3 Sources
Li-Jui Chen, Taiwan Semiconductor Manufacturing Company Ltd.
 (Taiwan)
Michael J. Lercel, SEMATECH Inc. (United States)
- 4 Mask I
Frank Goodwin, SEMATECH Inc. (United States)
Naoya Hayashi, Dai Nippon Printing Company, Ltd. (Japan)
- 5 Resist Outgassing
Soichi Inoue, EUVL Infrastructure Development Center, Inc. (Japan)
Kurt G. Ronse, IMEC (Belgium)
- 6 Optics and Metrology
Katsuhiko Murakami, Nikon Corporation (Japan)
Winfried Kaiser, Carl Zeiss SMT GmbH (Germany)
- 7 OPC and Modeling
Gregory R. McIntyre, IBM Corporation (United States)
Eric M. Panning, Intel Corporation (United States)
- 8 EUV Resists
Chris S. Ngai, Applied Materials, Inc. (United States)
Thomas I. Wallow, GLOBALFOUNDRIES Inc. (United States)

- 9 High NA and Magnification
Ted Liang, Intel Corporation (United States)
Jan Hendrik Peters, Carl Zeiss SMS GmbH (Germany)
- 10 Mask II
Stanley E. Stokowski, KLA-Tencor Corporation (United States)
Tsutomu Shoki, HOYA Corporation (Japan)
- 11 Invited II
Daniel A. Corliss, IBM Corporation (United States)
Seong-Sue Kim, SAMSUNG Electronics Company, Ltd. (Korea, Republic of)
- Poster Session
Patrick P. Naulleau, Lawrence Berkeley National Laboratory (United States)
Obert R. Wood II, GLOBALFOUNDRIES Inc. (United States)